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Sub B
b) a semiconductor component formed in the silicon layer overlying a portion of the substrate in which silicon has been removed by etching, and

c) a metal layer in the portion of the substrate in which silicon has been removed by etching, the metal layer abutting the silicon oxide layer and providing heat removal from the component, the silicon oxide layer electrically insulating the metal layer from the semiconductor component.

✓ Cancel claims 16-20.

A2
21. (Amended) The semiconductor device as defined by claim 15, wherein the metal layer comprises a refractory metal.

22. (Amended) The semiconductor device as defined by claim 21, wherein the metal layer comprises gold, aluminum, or copper over the refractory metal.

REMARKS

Independent claim 15 (amended) and dependent claims 21-23 remain in the application with claim 15 amended to improve form and overcome the rejection under 35 U.S.C. 112, second paragraph, and to include the limitations of claim 20. Claim 21 is now dependent from claim 15, and claim 22 is amended to expand the list of metal layers similar to claim 18, now canceled.

Reconsideration is respectfully requested for claims 15 and 21-23 as amended.

The Examiner has alleged that the declaration is defective for failing to include the mailing or Post Office address of the inventor.

This objection is believed to be in error since the mailing or Post Office address is in an application data sheet which was submitted with the application as filed.

Claims 15-23 have been rejected under 35 U.S.C. 112, second paragraph, as being indefinite, the Examiner noting specific objections in claim 15 lines 2 and 3.

This rejection is respectfully traversed for claims 15 and 21-23 as amended. The silicon oxide layer antecedent is now provided.